Amendments to the Specification

Please replace the second and third paragraphs on page 7 with the following:

Now, a passivation or barrier layer 16 is formed over the metal lines and planarized. Now, the key features of the present invention will be described. A first dielectric layer 18 is deposited over the barrier layer 16 to a thickness of between about 6000 and 20,000 Angstroms. This dielectric layer 18 comprises a low dielectric constant organic material, such as polyimides, hydrido organo siloxane polymer (HOSP) by AlliedSignal, Inc., SILK, a polyphenylene polymer by Dow Chemical, FLARE, a poly(arylene) ether by AlliedSignal, Inc., BCB, methylsilsesquioxane (MSQ), or any organic polymers. The dielectric constant should be less than about 3.5.

Next, a second dielectric layer 20 is deposited to a thickness of between about 6000 and 20,000 Angstroms. The second dielectric layer 20 comprises a low dielectric constant inorganic material, such as fluorinated silicate glass (FSG), carbon-doped FSG, nitrogen-doped FSG, CORAL, a carbon-doped oxide film by Novellus Systems, Inc., BLACK Diamond, a silicon oxide-based CVD low k film by Applied Materials, Trimethylsilane (Z3MS) by Air Products, XLK, a hydrogen silsesquioxane based material (by Dow Corning), and hydrogen silsesqioxane (HSQ). The dielectric constant should be less than about 3.5. Alternatively, the first dielectric layer could be inorganic and the second layer could be organic.